

IN THE CLAIMS:

1. (Previously Presented) A cleaning method for a vapor phase deposition apparatus for forming film onto a substrate by introducing film forming gas into a chamber via a shower head, comprising:

activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves, and then introducing the cleaning gas into a chamber;

raising a temperature of a shower head to a temperature greater than that used when forming a film on a substrate; and

removing a deposit comprising tungsten and silicon.

2. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises restricting a supply of a cooling medium to the shower head.

3. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 2, wherein raising the temperature of the shower head further comprises heating the shower head by a heater.

4. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises heating the shower head by a heater.

5. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein the temperature of the shower head is raised to about 50°C or above.

6. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein the film forming gas includes gas consisting of a compound containing tungsten atoms, and the temperature of the shower head is raised to about 70°C or above.

7-13. (Canceled)